

AMENDMENTS TO THE CLAIMS

1-18 (canceled)

19 (currently amended) A surface acoustic wave filter comprising: where
a plurality of surface acoustic wave resonators including a comb electrode
and a grating reflector are coupled on a piezoelectric substrate, and wherein
a dielectric film is formed on a surface of at least one of the surface
acoustic wave resonators,
wherein the dielectric film is not formed on a surface of at least ~~another~~
one other of the surface acoustic wave resonators, and
wherein a capacity ratio of the at least one surface acoustic wave resonator
having the dielectric film is set higher than a capacity ratio ~~that~~ of the at least one other
surface acoustic wave resonator having no dielectric film.

20 (currently amended) The surface acoustic wave filter of claim 19,
wherein a resonance frequency of the at least one surface acoustic wave
resonator having the dielectric film is set higher than that of the at least one other surface
acoustic wave resonator having no dielectric film.

21 (currently amended) The surface acoustic wave filter of claim 19,
wherein a resonance frequency of the at least one surface acoustic wave
resonator having the dielectric film is set lower than that of the at least one other surface
acoustic wave resonator having no dielectric film.

22 (currently amended) The surface acoustic wave filter of claim 19,
wherein the surface acoustic wave resonators are coupled in series and in
parallel to form a ladder type filter structure, and
wherein the dielectric film is formed on at least one of the surface acoustic
wave resonators coupled in series or on at least one of the surface acoustic wave
resonators coupled in parallel.

23 (previously presented) The surface acoustic wave filter of claim 19,
wherein the dielectric film is a silicon dioxide film.

24 (currently amended) A surface acoustic wave (SAW) SAW duplexer employing the
surface acoustic wave filter of claim 19.

25 (canceled)

26 (currently amended) A~~The~~ surface acoustic wave (SAW) SAW duplexer
comprising:~~of claim 25~~

a transmission filter;

a reception filter; and

a phase shifter,

wherein each of the transmission filter and reception filter has a ladder
type structure where surface acoustic wave resonators are coupled in series and in
parallel,

wherein depending on which side of each pass band requires a steeper
filter characteristic, a dielectric film is formed on at least one of the surface acoustic wave
resonators coupled in series or on at least one of the surface acoustic wave resonators
coupled in parallel,

wherein the SAW duplexer has a frequency allocation where a
transmission band lies on a low frequency side and a reception band lies on a high
frequency side,

wherein the transmission filter has a structure where the dielectric film is
formed on a surface of at least one of the surface acoustic wave resonators coupled in
series, and

wherein the reception filter has a structure where the dielectric film is
formed on a surface of at least one of the surface acoustic wave resonators coupled in
parallel.

27 (currently amended) ~~A~~The surface acoustic wave (SAW)SAW duplexer comprising:~~of claim 25~~

a transmission filter;

a reception filter; and

a phase shifter,

wherein each of the transmission filter and reception filter has a ladder type structure where surface acoustic wave resonators are coupled in series and in parallel,

wherein depending on which side of each pass band requires a steeper filter characteristic, a dielectric film is formed on at least one of the surface acoustic wave resonators coupled in series or on at least one of the surface acoustic wave resonators coupled in parallel,

wherein the SAW duplexer has a frequency allocation where a transmission band lies on a high frequency side and a reception band lies on a low frequency side,

wherein the transmission filter has a structure where the dielectric film is formed on a surface of at least one of the surface acoustic wave resonators coupled in parallel, and

wherein the reception filter has a structure where the dielectric film is formed on a surface of at least one of the surface acoustic wave resonators coupled in series.